

B1  
Concl'd  
C1  
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Concl'd

2. (Twice Amended) A semiconductor device comprising a TFT containing an active layer having a channel forming region,  
wherein the channel forming region has a convex portion or a concave portion extending in a channel width direction, and  
wherein zero or one grain boundary is contained in the channel forming region.

3. (Twice Amended) A semiconductor device comprising a TFT containing an active layer having a channel forming region,  
wherein the channel forming region has a convex portion or a concave portion extending in a channel width direction, and  
wherein the number of grain boundaries crossing the channel forming region in the width direction of the channel is zero or one.

B2  
Sub  
C2

11. (Amended) A semiconductor device comprising:  
a semiconductor layer formed over a substrate; and  
a channel forming region and source and drain regions formed in said semiconductor layer,  
wherein said channel forming region has at least one convex portion extending in a direction perpendicular to a channel length direction.

12. (Amended) A semiconductor device comprising:  
a semiconductor layer formed over a substrate; and  
a channel forming region and source and drain regions formed in said semiconductor layer,  
wherein said channel forming region has at least one concave portion extending in a direction perpendicular to a channel length direction.

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13. (Amended) A semiconductor device comprising:  
a semiconductor layer formed over substrate; and  
a channel forming region and source and drain regions formed in said semiconductor layer,  
wherein said channel forming region has at least one convex portion extending in a channel width direction.

14. (Amended) A semiconductor device comprising:  
a semiconductor layer formed over a substrate; and  
a channel forming region and source and drain regions formed in said semiconductor layer,  
wherein said channel forming region has at least one concave portion extending in a channel width direction.

15. (Amended) A semiconductor device comprising:  
a semiconductor layer formed over a substrate; and  
a channel forming region and source and drain regions formed in said semiconductor layer,  
wherein said channel forming region has at least one convex portion extending in a direction perpendicular to a carrier flow direction.

16. (Amended) A semiconductor device comprising:  
a semiconductor layer formed over a substrate;  
a channel forming region and source and drain regions formed in said semiconductor layer; and  
wherein said channel forming region has at least one concave portion extending in a direction perpendicular to a carrier flow direction.